

# Phase Control Thyristors (Hockey PUK Version), 960 A



E-PUK (TO-200AB)

PRIMARY CHARACTERISTICS						
I <sub>T(AV)</sub> 960 A						
V <sub>DRM</sub> /V <sub>RRM</sub>	400 V, 600 V					
$V_{TM}$	1.58 V					
I <sub>GT</sub>	100 mA					
T <sub>J</sub>	-40 °C to +150 °C					
Package	E-PUK (TO-200AB)					
Circuit configuration	Single SCR					

#### **FEATURES**

- · Center amplifying gate
- Metal case with ceramic insulator
- International standard case E-PUK (TO-200AB)



- Extended temperature range
- Low profile hockey PUK to increase current-carrying capability
- Designed and qualified for industrial level
- Material categorization: for definitions of compliance please see <a href="https://www.vishay.com/doc?99912"><u>www.vishay.com/doc?99912</u></a>

#### **TYPICAL APPLICATIONS**

- DC motor controls
- Controlled DC power supplies
- AC controllers

MAJOR RATINGS AND CHARACTERISTICS							
PARAMETER	TEST CONDITIONS	VALUES	UNITS				
1		960	А				
$I_{T(AV)}$	T <sub>hs</sub>	80	°C				
1		2220	А				
I <sub>T</sub> (RMS)	T <sub>hs</sub>	25	°C				
1	50 Hz	12 500	۸				
I <sub>TSM</sub>	60 Hz	13 000	Α				
I <sup>2</sup> t	50 Hz	782	kA <sup>2</sup> s				
1-1	60 Hz	713	KA-S				
V <sub>DRM</sub> /V <sub>RRM</sub>		400 to 600	V				
t <sub>q</sub>	Typical	100	μs				
TJ		-40 to 150	°C				

#### **ELECTRICAL SPECIFICATIONS**

VOLTAGE RATINGS										
TYPE NUMBER	VOLTAGE CODE	V <sub>DRM</sub> /V <sub>RRM</sub> , MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE V	V <sub>RSM</sub> , MAXIMUM NON-REPETITIVE PEAK VOLTAGE V	$I_{DRM}/I_{RRM}$ MAXIMUM AT $T_J = T_J$ MAXIMUM mA						
VS-ST380CHC	04	400	500	100						
VO-010000110	06	600	700	100						



ABSOLUTE MAXIMUM RATINGS	S					
PARAMETER	SYMBOL		TEST CON	IDITIONS	VALUES	UNITS
Maximum average on-state current	L	180° condu	ction, half sine v	vave	960 (440)	Α
at heatsink temperature	$I_{T(AV)}$	double side	(single side) co	oled	80 (110)	°C
Maximum RMS on-state current	I <sub>T(RMS)</sub>	DC at 25 °C	heatsink tempe	erature double side cooled	2220	
		t = 10 ms	No voltage		12 500	
Maximum peak, one-cycle	ı	t = 8.3 ms	reapplied		13 000	A kA <sup>2</sup> s
non-repetitive surge current	I <sub>TSM</sub>	t = 10 ms	100 % V <sub>RRM</sub>		10 500	
		t = 8.3 ms	reapplied	Sinusoidal half wave, initial $T_J = T_J$ maximum	11 000	
2.6.6.	l <sup>2</sup> t	t = 10 ms	No voltage reapplied		782	
		t = 8.3 ms			713	
Maximum I <sup>2</sup> t for fusing		t = 10 ms	100 % V <sub>RRM</sub>		553	
		t = 8.3 ms	reapplied		505	
Maximum l²√t for fusing	I <sup>2</sup> √t	t = 0.1 to 10	ms, no voltage	reapplied	7820	kA²√s
Low level value of threshold voltage	V <sub>T(TO)1</sub>	(16.7 % x π	$x I_{T(AV)} < I < \pi x$	$I_{T(AV)}$ ), $T_J = T_J$ maximum	0.85	V
High level value of threshold voltage	V <sub>T(TO)2</sub>	$(I > \pi \times I_{T(AV)})$	$(J)$ , $T_J = T_J$ maxin	num	0.88	V
Low level value of on-state slope resistance	r <sub>t1</sub>	(16.7 % x π	$(16.7 \% \times \pi \times I_{T(AV)} < I < \pi \times I_{T(AV)}), T_J = T_J \text{ maximum}$			0
High level value of on-state slope resistance	r <sub>t2</sub>	$(I > \pi \times I_{T(AV)}), T_J = T_J \text{ maximum}$			0.24	mΩ
Maximum on-state voltage	$V_{TM}$	$I_{pk} = 2900 \text{ A}, T_J = T_J \text{ maximum}, t_p = 10 \text{ ms sine pulse}$			1.58	V
Maximum holding current	I <sub>H</sub>	T 05 °C	T <sub>.1</sub> = 25 °C, anode supply 12 V resistive load			A
Typical latching current	ΙL	1 J = 25 °C,	anoue supply 1	z v resistive idad	1000	mA

SWITCHING								
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS				
Maximum non-repetitive rate of rise of turned-on current	dI/dt	Gate drive 20 V, 20 $\Omega$ , $t_r \le 1~\mu s$ $T_J = T_J$ maximum, anode voltage $\le 80~\%~V_{DRM}$	1000	A/μs				
Typical delay time	t <sub>d</sub>	Gate current 1 A, $dl_g/dt = 1$ A/ $\mu$ s $V_d = 0.67 \% V_{DRM}$ , $T_J = 25 \ ^{\circ}C$	1.0	110				
Typical turn-off time	tq	$I_{TM}$ = 550 A, $T_J$ = $T_J$ maximum, dl/dt = 40 A/ $\mu$ s, $V_R$ = 50 V, dV/dt = 20 V/ $\mu$ s, gate 0 V 100 $\Omega$ , $t_p$ = 500 $\mu$ s	100	μs				

BLOCKING							
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Maximum critical rate of rise of off-state voltage	dV/dt	$T_J = T_J$ maximum linear to 80 % rated $V_{DRM}$	500	V/µs			
Maximum peak reverse and off-state leakage current	I <sub>RRM</sub> , I <sub>DRM</sub>	$T_J = T_J$ maximum, rated $V_{DRM}/V_{RRM}$ applied	100	mA			



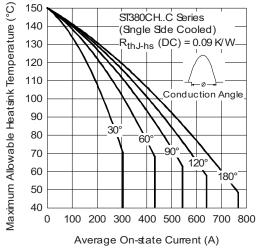
TRIGGERING							
PARAMETER	SYMBOL	TE	ST CONDITIONS	VALUES		UNITS	
PARAMETER	STINIBUL	16	51 CONDITIONS	TYP.	MAX.	UNITS	
Maximum peak gate power	$P_{GM}$	$T_J = T_J$ maximum,	$t_p \le 5 \text{ ms}$	10	0.0	w	
Maximum average gate power	P <sub>G(AV)</sub>	$T_J = T_J$ maximum,	f = 50 Hz, d% = 50	2.	.0	VV	
Maximum peak positive gate current	I <sub>GM</sub>	T <sub>J</sub> = T <sub>J</sub> maximum,	$t_p \le 5 \text{ ms}$	3.	.0	Α	
Maximum peak positive gate voltage	+ V <sub>GM</sub>	T - T movimum	+ < 5 ma	2	0	V	
Maximum peak negative gate voltage	- V <sub>GM</sub>	ij = ij maximum,	$T_J = T_J$ maximum, $t_p \le 5$ ms				
		T <sub>J</sub> = -40 °C		200	-		
DC gate current required to trigger	I <sub>GT</sub>	T <sub>J</sub> = 25 °C	Maximum required gate trigger/	100	200	mA	
		T <sub>J</sub> = 150 °C	current/voltage are the lowest value which will trigger all units	40	-		
		T <sub>J</sub> = -40 °C		2.5	-		
DC gate voltage required to trigger	$V_{GT}$	T <sub>J</sub> = 25 °C	12 V anode to cathode applied	1.8	3.0	٧	
		T <sub>J</sub> = 150 °C		1.0	-		
DC gate current not to trigger	I <sub>GD</sub>	T T	Maximum gate current/voltage not to trigger is the maximum	10		mA	
DC gate voltage not to trigger	V <sub>GD</sub>	$T_J = T_J \text{ maximum}$	value which will not trigger any unit with rated V <sub>DRM</sub> anode to cathode applied	0.25		V	

THERMAL AND MECHANICAL SPECIFICATIONS							
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Maximum operating junction temperature range	TJ		-40 to 150	°C			
Maximum storage temperature range	T <sub>Stg</sub>		-40 10 150				
Maximum thermal resistance, junction to heateigh	В	DC operation single side cooled	0.09				
Maximum thermal resistance, junction to heatsink	R <sub>thJ-hs</sub>	DC operation double side cooled	0.04	K/W			
Maximum thermal resistance, case to heatsink	R <sub>thC-hs</sub>	DC operation single side cooled	0.02				
Maximum thermal resistance, case to heatsink		DC operation double side cooled	0.01				
Mounting force, ± 10 %			9800 (1000)	N (kg)			
Approximate weight			83	g			
Case style		See dimensions - link at the end of datasheet	E-PUK (TO-2	200AB)			

△R <sub>thJ-hs</sub> CONDUCTION								
CONDUCTION ANGLE	CONDUCTION	RECTANGULA	R CONDUCTION	TECT COMPITIONS	UNITS			
CONDUCTION ANGLE	SINGLE SIDE	DOUBLE SIDE	SINGLE SIDE	DOUBLE SIDE	TEST CONDITIONS	UNITS		
180°	0.010	0.011	0.007	0.007				
120°	0.012	0.012	0.012	0.013				
90°	0.015	0.015	0.016	0.017	$T_J = T_J$ maximum	K/W		
60°	0.022	0.022	0.023	0.023				
30°	0.036	0.036	0.036	0.037				

#### Note

<sup>•</sup> The table above shows the increment of thermal resistance R<sub>thJ-hs</sub> when devices operate at different conduction angles than DC



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Fig. 1 - Current Ratings Characteristics

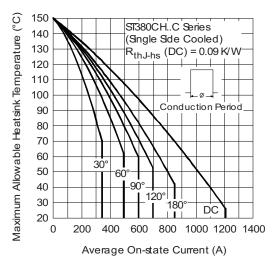


Fig. 2 - Current Ratings Characteristics

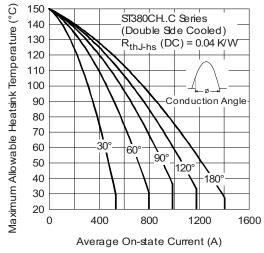


Fig. 3 - Current Ratings Characteristics

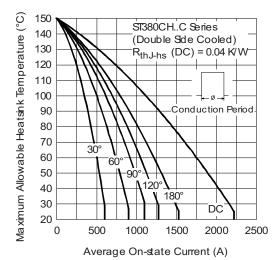


Fig. 4 - Current Ratings Characteristics

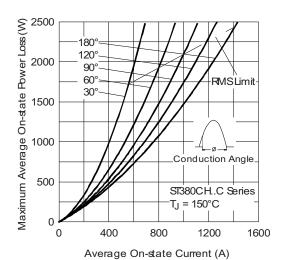


Fig. 5 - On-State Power Loss Characteristics

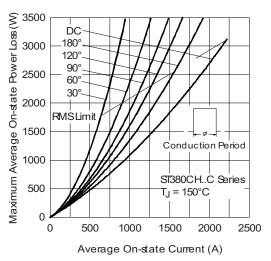
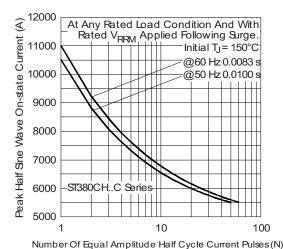


Fig. 6 - On-State Power Loss Characteristics



Number of Equal Amplitude Fall Cycle Current Fulses

Fig. 7 - Maximum Non-Repetitive Surge Current Single and Double Side Cooled

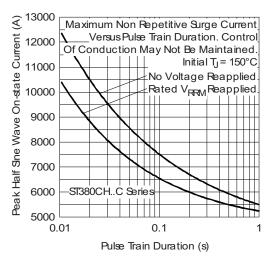


Fig. 8 - Maximum Non-Repetitive Surge Current Single and Double Side Cooled

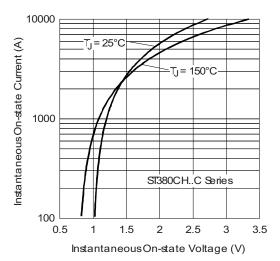


Fig. 9 - On-State Voltage Drop Characteristics

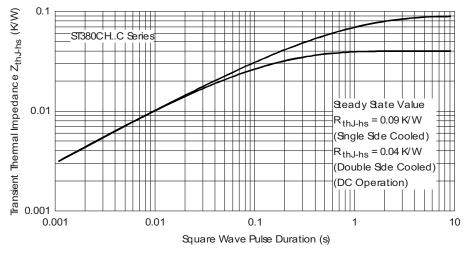


Fig. 10 - Thermal Impedance  $Z_{\text{thJ-hs}}$  Characteristics

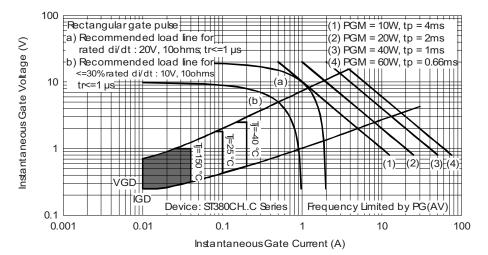


Fig. 11 - Gate Characteristics

#### **ORDERING INFORMATION TABLE**

Device code	VS-	ST	38	0	СН	06	С	1	•
	1	2	3	4	5	6	7	8	9

1 - Vishay Semiconductors product

2 - Thyristor

3 - Essential part number

4 - 0 = converter grade

5 - CH = ceramic PUK, high temperature

6 - Voltage code x 100 = V<sub>RRM</sub> (see Voltage Ratings table)

7 - C = PUK case E-PUK (TO-200AB)

8 - 0 = eyelet terminals (gate and auxiliary cathode unsoldered leads)

1 = fast-on terminals (gate and auxiliary cathode unsoldered leads)

2 = eyelet terminals (gate and auxiliary cathode soldered leads)

3 = fast-on terminals (gate and auxiliary cathode soldered leads)

9 - Critical dV/dt: • None = 500 V/µs (standard selection)

• L = 1000 V/µs (special selection)

LINKS TO RELAT	ED DOCUMENTS
Dimensions	http://www.vishay.com/doc?95075

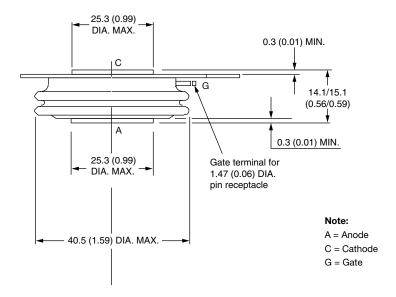


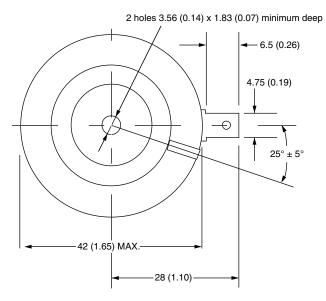
# E-PUK (TO-200AB)

#### **DIMENSIONS** in millimeters (inches)

Anode to gate

Creepage distance: 11.18 (0.44) minimum Strike distance: 7.62 (0.30) minimum





Quote between upper and lower pole pieces has to be considered after application of mounting force (see thermal and mechanical specification)



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